

ABSTRACT

Image sensing devices including pixel isolation structures are disclosed. In an embodiment, an image sensing device includes a first pixel and a second pixel. The first pixel includes a first
5 photoelectric conversion region configured to detect light of a first wavelength range, and a first pixel isolation structure that surrounds the first photoelectric conversion region and has a first width. The second pixel includes a second photoelectric conversion region configured to detect light of the first wavelength range, and a second
10 pixel isolation structure that surrounds the second photoelectric conversion region and has a second width smaller than the first width.

FIG.3